

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

2SB1481

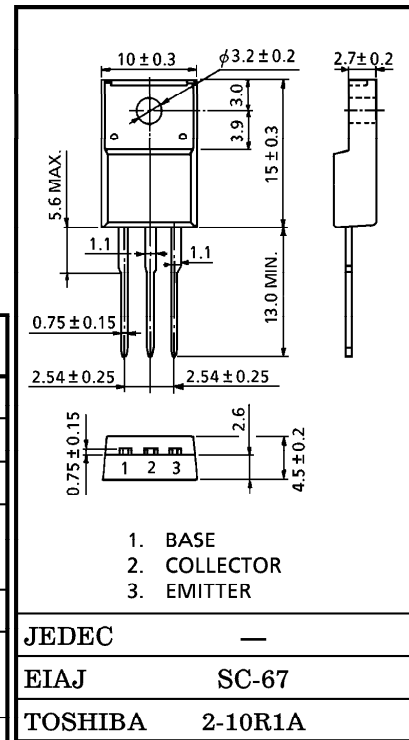
SWITCHING APPLICATIONS

- High DC Current Gain
: $h_{FE} = 2000$ (Min.) ($V_{CE} = -2V$, $I_C = -1.5A$)
- Low Saturation Voltage : $V_{CE(sat)} = -1.5V$ (Max.) ($I_C = -3A$)
- Complementary to 2SD2241

MAXIMUM RATINGS ($T_a = 25^\circ C$)

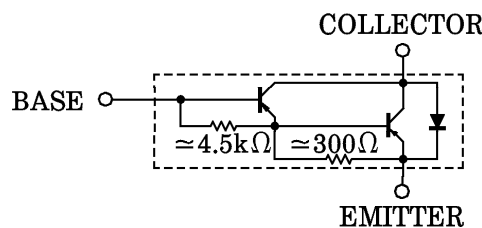
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	DC	I_C	± 4
	Pulse	I_{CP}	± 6
Base Current	I_B	-0.3	A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	2.0
	$T_c = 25^\circ C$		25
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

Unit in mm



Weight : 1.7g

EQUIVALENT CIRCUIT



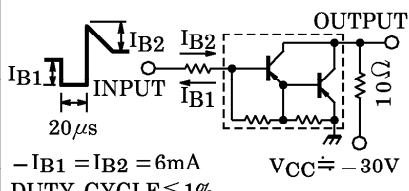
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = -100V, I _E = 0	—	—	-2.0	μA
Emitter Cut-off Current		IEBO	V _{EB} = -5V, I _C = 0	—	—	-2.5	mA
Collector-Emitter Breakdown Voltage		V _{(BR) CEO}	I _C = -10mA, I _B = 0	-100	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = -2V, I _C = -1.5A	2000	—	—	
		h _{FE} (2)	V _{CE} = -2V, I _C = -3A	1000	—	—	
Collector-Emitter Saturation Voltage		V _{CE (sat)}	I _C = -3A, I _B = -6mA	—	—	-1.5	V
Base-Emitter Saturation Voltage		V _{BE (sat)}	I _C = -3A, I _B = -6mA	—	—	-2.0	V
Collector-Emitter Reverse Voltage		V _{ECO}	I _C = 1A, I _B = 0	—	—	2.0	V
Switching Time	Turn-on Time	t _{on}	 <p> $-I_{B1} = I_{B2} = 6\text{mA}$ DUTY CYCLE $\leq 1\%$ </p>	—	0.15	—	μs
	Storage Time	t _{stg}		—	0.80	—	
	Fall Time	t _f		—	—	0.40	

